# IRPP3624-12A POWIR+ Chipset Reference Design \#0612 

## D $\cap$ CHIPSET

SIMPLICITY IN POWER DESIGN
12Amp Single Phase Synchronous Buck POWIR+ ${ }^{\text {TM }}$ Chipset Reference Design using IR3624MPBF PWM \& Driver IC and IRF7823 and IRF7832Z MOSFET

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## Introduction

The IRPP3624-12A is an optimized POWIR+ ${ }^{\text {TM }}$ Chipset reference design, targeted at, low power synchronous buck applications up to 12A output current. The IRPP3624-12A uses International Rectifier's IR3624MPBF single channel, 600 kHz fixed switching frequency PWM controller in a 10-pin MLPD and IRF7823 and IRF7832Z MOSFET. This reference design has built-in power design expertise regarding component selection and PCB layout, and is representative of a realistic final embedded synchronous buck design, intended to simplify the design in effort without unnecessary design iterations. The design is optimized for 12 V input and 1.8 V output @ 12A, including considerations on layout and passive \& magnetic component selection. The IRPP362412A delivers the complete 12A design in less than $0.7 \mathrm{in}^{2}$ board area at up to $84 \%$ full load electrical efficiency.

International Rectifier also offers the POWIR+ Chipset on-line design tool (http:/lpowirplus.irf.com) allowing the customization of the IRPP3624-12A reference design to meet individual requirements. Based on specific inputs, the POWIR+ Chipset on-line design tool will provide a tailored schematic and bill of materials, from which the engineer can run a full suite of on-line design simulations, and then order the fully assembled and tested customized reference design (see details on page 14).

## Design Details

The IRPP3624-12A reference design is optimized for an input voltage range of 10.8 V to 13.2 V and an output voltage of 1.8 V at a maximum of 12 A load current,
using the IRF7823 and IRF7832Z MOSFET.

The 600 kHz switching frequency allows the selection of reduced size power components. All the essential components that contribute to a low cost compact solution are enclosed by the rectangular box shown on the PCB, showing a total solution size of $0.625^{\prime \prime}$ x 1.125 " ( 0.7 " sq ). The electrical connection diagram is shown in figure 1 and the corresponding circuit schematic is shown in figure 2.


Figure 1: IRPP3624-12AElectrical Connection Diagram

## Input/Output Connections

J1: Input power connection terminal
J2: Input power return preferred connection terminal
J3: Output power return preferred connection terminal
J4: Output power connection terminal
J5: External bias power connection terminal. This terminal is unused for standard reference design configuration.
J6: External bias power return preferred connection terminal. This terminal is unused for standard reference design configuration.

## Start-Up Procedure

The 12 V input power is connected between terminals J 1 and J 2 and the $1.8 \mathrm{~V}, 12 \mathrm{~A}$ output power is obtained through terminals J 3 and J 4 .
The $\mathrm{V}_{\mathrm{Cc}}$ and $\mathrm{V}_{\mathrm{C}}$ pins are the low side driver and high side driver power input pins respectively. The $\mathrm{V}_{\mathrm{cc}}$ pin also includes the housekeeping power of the PWM controller. An under-voltage lockout (UVLO) feature is associated with each of these pins, which is set to 4.2 V for $\mathrm{V}_{\mathrm{cc}}$ and 3.2 V for $\mathrm{V}_{\mathrm{c}}$. A charge pump circuit comprised of C11, D1, and C12 applies adequate voltage to the $\mathrm{V}_{\mathrm{C}}$ pin to allow fast driving capability, hence reducing the switching losses of the control FET, IRF7823PBF. A $25 \Omega$ resistor (R11 in parallel with R12) is added in series with the charge pump circuit to maintain the $\mathrm{V}_{\mathrm{C}}$ voltage below 20 V to reduce the temperature of the PWM controller IC.
Upon application of the input power, the output starts ramping up to regulation within 4 ms . The ramping time can be adjusted through the soft start capacitor C5. The output voltage of the synchronous buck regulator is set to 1.8 V using the internal 0.6 V reference voltage.
The following equations are used to calculate the MOSFET power loss. Refer to the IRF7823PBF and IRF7832ZPBF datasheets to select the parametric values of the power loss equations terms.

## Control FET Losses:

Eq (1):
$P_{Q_{1}}=I_{Q_{1}} r m s^{2} \cdot R_{D Q 1} \cdot R_{D n}+\left(I_{o} \cdot \frac{Q_{s m}}{I_{g 1}} \cdot V_{i n}+Q_{g Q 1} \cdot V_{d d}+Q_{\text {ossal } 1} \cdot V_{i n}\right) \cdot F_{\text {sW }}$

## Synchronous FET Losses:

Eq (2):
$P_{Q_{2}}=I_{Q_{2}} r m s^{2} \cdot R_{D Q_{2}} \cdot R_{D n}+\left(\frac{Q_{\text {oss } Q^{2}}}{2} \cdot V_{\text {in }}+Q_{g Q_{2} 2} \cdot V_{d d}+Q_{r Q_{Q 2}} \cdot V_{\text {in }}\right) \cdot F_{S W}$

## Deadtime losses:

Eq (3):

$$
P_{t d}=V_{S D} \cdot I_{o} \cdot t_{d} \cdot F_{s w}
$$

## Total FET Iosses:

Eq (4):

$$
P_{\text {FET_total }}=P_{Q 1}+P_{Q 2}+P_{t d}
$$

Where,
$\mathrm{l}_{\mathrm{Q} 1 \text { rms }}$ and $\mathrm{I}_{\mathrm{Q} 2 r m s}$ are the rms currents for control and sync FETs respectively, in Amps
$\mathrm{I}_{\mathrm{O}}$ is the output load current in Amps
$R_{D}$ is the $R_{D S O N}$ in ohms of the FETs and $R_{D n}$ is the normalized $R_{D S O N}$ factor vs temperature extracted from the IRF7823PBF and IRF7832ZPBF datasheets.
$\mathrm{Q}_{\text {sw }}$ is the FET switch charge in nC
$\mathrm{V}_{\text {IN }}$ is the input voltage of the sync buck converter
$\mathrm{Q}_{\mathrm{g}}$ is the total gate charge in nC .
$\mathrm{V}_{\mathrm{dd}}$ is the FET drive voltage, which is 8 V .
$\mathrm{I}_{\mathrm{g}}$ is the drive current which is 0.5 A .
Qoss is the FET output charge in nC .
$\mathrm{Q}_{\mathrm{rr}}$ is the sync FET internal body diode reverse recovery charge in nC
$\mathrm{V}_{\mathrm{SD}}$ is the sync FET internal body diode forward voltage drop in volts. $\mathrm{F}_{\mathrm{sw}}$ is the switching frequency of the sync buck converter in hertz.
td is the dead time caused by the PWM controller IC in seconds. This parameter is specified in IR3624MPBF datasheet.

For design calculations related to programming the output voltage and the soft start time, selection of input/output capacitors and output inductor and control loop compensation, refer to the guidelines outlined in the IR3624MPBF PWM controller datasheet.

IR's online design tool POWIR ${ }^{+}$should be used to customize a design for applications outside the standard 10.8 V to 13.2 V input range and 1.8 V output, and for varied design goal objectives.

## Layout Considerations

The IRPP3624-12A reference design PCB layout offers compact design with minimum parasitics at 600 kHz switching frequency. The board is designed with 4 layers using 1 oz copper weight per layer. Figures 3a through 3d represent the layout of each layer. To minimize the parasitics, the following was observed:

1. The switch node connection path is made as short as possible by placing the output inductor L1 close to the drain of the synchronous FET.
2. The input decoupling 10uF ceramic capacitors C1 through C4, are placed across the drain of the control FET and the PGND/
3. A solid ground plane is furnished in mid-layer 2. The connection of the signal ground to power ground is done at a single point in the bottom layer as shown in figure 3d.
4. The feedback track from the output $V_{\text {out }}$ to FB pin of the IC is routed as far away from noise generating traces as possible in mid-layer 2 as shown in figure 3c.


Figure 2: Schematic Diagram for IRPP3624-12AReference Design

| QTY | REF <br> DESIGNATOR | DESCRIPTION | SIZE | MFR | PART NUMBER |
| :---: | :---: | :---: | :---: | :---: | :---: |
| 1 | C6 | Capacitor, ceramic, 47pF, 50V,NPO, 5\% | 0603 | KOA | NPO0603HTTD470J |
| 1 | C8 | Capacitor, ceramic, 1.8nF, 50V,X7R, 10\% | 0603 | KOA | X7R0603HTTD182K |
| 1 | C7 | Capacitor, ceramic, 6.8nF,50V,X7R,10\% | 0603 | KOA | X7R0603HTTD682K |
| 4 | $\begin{gathered} \hline \text { C5, C10, C11, } \\ \text { C12 } \end{gathered}$ | $\begin{gathered} \hline \text { Capacitor, ceramic, } 0.1 \mu \mathrm{~F}, 50 \mathrm{~V}, \\ \mathrm{X} 7 \mathrm{R}, 10 \% \\ \hline \end{gathered}$ | 0603 | TDK | C1608X7R1H104K |
| 1 | C13 | $\begin{gathered} \hline \text { Capacitor, ceramic, } 1.0 \mu \mathrm{~F}, 16 \mathrm{~V}, \\ \text { X5R, } 10 \% \end{gathered}$ | 0603 | TDK | C1608X5R1C105K |
| 3 | C15, C16, C17 | $\begin{gathered} \text { Capacitor, ceramic, 47uF, 6.3V, } \\ \text { X5R, } 20 \% \\ \hline \end{gathered}$ | 1206 | TDK | C3216X5R0J476M |
| 3 | C1, C2, C3 | Capacitor, ceramic, $10 \mathrm{uF}, 16 \mathrm{~V}$, X5R, 20\% | 1206 | TDK | C3216X5R1C106M |
| 1 | C14 | Capacitor, POSCAP, 470uF, 6.3V $20 \%$ | 7343 | SANYO | 6TPB470M |
| 1 | D1 | Schottky Diode, 30V,200mA | SOT23 | IRF | BAT54S |
| 1 | D2 | Schottky Diode, 40V,1.5A | D64 | IRF | 10MQ040N |
| 3 | J1, J4, J5 | Red Banana Jacks-Insulated Solder Terminal | 4.44 mm | Johnson | 108-0902-001 |
| 3 | J2, J3, J6 | Black Banana Jacks-Insulated Solder Terminal | 4.44 mm | Johnson | 108-0903-001 |
| 4 | J1, J4, J5, J6 | Pan Head Slotted,screw 1/2" | - | McMaster-Carr | 91792A081 |
| 2 | J2, J3 | Pan Head Slotted,screw 1/4" | - | McMaster-Carr | 91792A077 |
| 6 | $\begin{gathered} \hline \mathrm{J} 1, \mathrm{~J} 2, \mathrm{~J} 3, \mathrm{J4}, \\ \mathrm{J5}, \mathrm{~J} 6 \end{gathered}$ | Machine Screw Hex Nuts | - | McMaster-Carr | 91841A003 |
| 1 | L1 | 0.6uH,8A,20m $\Omega$ | $\begin{gathered} 10 \mathrm{~mm} \times \\ 10 \mathrm{~mm} \times 4 \mathrm{~mm} \end{gathered}$ | DELTA | MPL104-0R6 |
| 1 | R8 | Resistor,thick film, $0 \Omega$ | 0805 | ROHM | MCR10EZHJOO0 |
| 1 | R9 | Resistor,thick film, $0 \Omega$ | 0603 | ROHM | MCR03EZHJOOO |
| 1 | R13 | Resistor,thick film, $0 \Omega$ | 1206 | KOA | RM73Z2B000 |
| 1 | R5 | Resistor,thick film,1ת, 5\% | 0805 | ROHM | MCR10EZHJ1R0 |
| 1 | R6 | Resistor,thick film,20ת, 1\% | 0603 | KOA | RK73H1JLTD20R0F |
| 1 | R4 | Resistor,thick film,681 ${ }^{\text {, }} 1 \%$ | 0603 | KOA | RK73H1JLTD6810F |
| 1 | R1 | Resistor,thick film, $5.11 \mathrm{k} \Omega, 1 \%$ | 0603 | KOA | RK73H1JTTD5111F |
| 1 | R3 | Resistor,thick film, $4.22 \mathrm{k} \Omega$, 1\% | 0603 | KOA | RK73H1JLTD4221F |
| 1 | R2 | Resistor,thick film,8.45k $\Omega$, 1\% | 0603 | KOA | RK73H1JLTD8451F |
| 2 | R11,R12 | Resistor,thick film, $49.9 \Omega, 1 \%$ | 1206 | KOA | RK73H2B49R9F |
| 1 | R16 | Resistor,thick film, $6.19 \mathrm{k} \Omega, 1 \%$ | 0603 | KOA | RK73H1JLTD6191F |
| 1 | Q1 | $\mathrm{N}-\mathrm{FET}, 30 \mathrm{~V}, 8.7 \mathrm{~m} \Omega, 9.1 \mathrm{nC}$ | SO-8 | IRF | IRF7823PbF |
| 1 | Q2 | N-FET,30V,3.8m, ,30nC | SO-8 | IRF | IRF7832ZPbF |
| 1 | U1 | PWM Controller | SO-8 | IRF | IR3624MPBF |
| 6 | $\begin{gathered} \text { C4, C9, R7, } \\ \text { R10, R14, R15 } \\ \hline \end{gathered}$ | Not installed |  |  |  |

Table 1 - Complete Bill of Materials for IRPP3624-12AReference Design


Figure 3a: IRPP3624-12A Reference Design top layer placement and layout.


Figure 3b: IRPP3624-12A Reference Design mid-layer1 ground plane


Figure 3c: IRPP3624-12A Reference Design mid-layer2 layout.


Figure 3d: IRPP3624-12A Reference Design bottom layer layout.


Figure 4a: IRPP3624-12A Reference Design Electrical Efficiency


Figure 4b: IRPP3624-12A Reference Design Power Loss Curve


Figure 5: IRPP3624-12A Reference Design Thermograph at 12A load


Figure 6: IRPP3624-12A Reference Design Bode Plot of the Control Loop at 12A load.


Figure 7: Input ripple, $\mathrm{I}_{\mathrm{O}}=12 \mathrm{~A}$


Figure 8: Output ripple, $\mathrm{I}_{\mathrm{O}}=12 \mathrm{~A}$

## REFERENCE DESIGN



Figure 9: Output voltage transients, $50 \%$ load step, 6 A to 12 A to $6 \mathrm{~A}, \mathrm{di} / \mathrm{dt}=2.5 \mathrm{~A} / \mu \mathrm{s}$


Figure 10: Hiccup mode, response to output short circuit


Figure 11: Power up. $\mathrm{Ch} 1=\mathrm{V}_{\mathrm{IN}}, \mathrm{Ch} 2=\mathrm{V}_{\text {Out }}, \mathrm{Ch} 3=$ Soft Start


Figure 12: Power down. Ch1= $\mathrm{V}_{\mathrm{IN}}$, $\mathrm{Ch} 2=\mathrm{V}_{\mathrm{out}}, \mathrm{Ch} 3=$ Soft Start

| Part Number | Input <br> Voltage | Output <br> Voltage | Output <br> Current | Switching <br> Frequency | Power Semi BOM | Delivery <br> Time | Comments |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| IRPP3624-5A | 12 V | 3.3 V | 5 A | 600 kHz | IR3624M (MLPD-3x3) <br> IRF8910 (Dual SO-8) | 24-48 | Standard <br> Reference Design <br> Fixed BOM |
| IRPP3624-12A | 12 V | 1.8 V | 12 A | 600 kHz | IR3624M (MLPD-3x3) <br> IRF7823 (SO-8) <br> IRF7832Z (SO-8) | hrs | (SR |

Table 2 - Complete IRPP3624-xxA Reference Design Selector Table

